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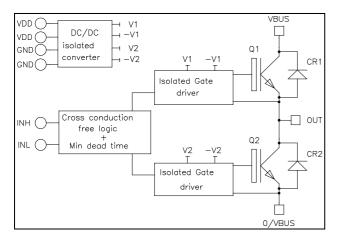


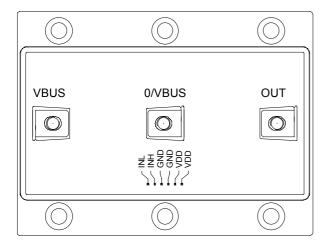






# Phase leg Intelligent Power Module





## $V_{CES} = 1200V$ $I_{C} = 300A$ @ $T_{C} = 80^{\circ}C$

#### Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier

#### **Features**

- Trench + Field Stop IGBT 3 Technology
  - Low voltage drop
  - Low tail current
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated

#### • Integrated Fail Safe IGBT Protection (Driver)

- Top Bottom input signals Interlock
- Isolated DC/DC Converter
- Low stray inductance
- M5 power connectors
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/μs)
- Galvanic Isolation: 3750V for the optocoupler 2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single V<sub>DD</sub>=5V supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- RoHS compliant

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### 1. Inverter Power Module

### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	440	
		$T_C = 80^{\circ}C$	300	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	1400	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 1150V	

#### **Electrical Characteristics**

	Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
	Lana	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25$ °C			500	μA
I <sub>CES</sub>	ICES	Zero Gate Voltage Concetor Current	$V_{CE} = 1200V$	$T_j = 125$ °C			750	μΑ
	V	Collector Emitter Saturation Voltage	$V_{\rm DD} = V_{\rm IN} = 5V$	$T_j = 25$ °C		1.7	2.1	17
	V <sub>CE(sat)</sub>	Conector Emitter Saturation Voltage	$I_{\rm C} = 300 A$	$T_{i} = 125^{\circ}C$		2		·

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		21		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		1.12		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		0.96		
$T_{\rm r}$	Rise Time	Inductive Switching (25°C)		40		ng
$T_{\mathrm{f}}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$ ; $I_C = 300A$		70		ns
$T_{\rm r}$	Rise Time	Inductive Switching (125°C)		45		ma
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$ $I_C = 300A$		90		ns
$E_{on}$	Turn-on Switching Energy			28		Т
$E_{\text{off}}$	Turn-off Switching Energy			32		mJ
$I_{sc}$	Short Circuit data	$V_{DD} = V_{IN} = 5V; V_{Bus} = 900V$ $t_p \le 10 \mu s; T_j = 125 ^{\circ}C$		1200		A
$R_{\text{thJC}}$	Junction to Case thermal resistance				0.09	°C/W

### Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_i = 25$ °C			250	μA
- Tun			$T_{i} = 125^{\circ}C$		200	500	
$l_{ m F}$	DC Forward Current		$Tc = 80^{\circ}C$		300		Α
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 300A$	$T_i = 25^{\circ}C$		1.6	2.1	V
<b>v</b> F			$T_{i} = 125^{\circ}C$		1.6		_ v
$t_{\rm rr}$	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$ $di/dt = 3500A/\mu s$	$T_j = 25$ °C		170		ns
ι <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 125^{\circ}C$		280		113
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^{\circ}C$		28		μC
Qrr	Reverse Recovery Charge		$T_j = 125$ °C		56		μС
$E_{rr}$	Reverse Recovery Energy		$T_j = 25$ °C		12		mJ
⊥rr			$T_{j} = 125^{\circ}C$		22		1113
$R_{thJC}$	Junction to Case Thermal Resistance					0.16	°C/W

#### 2. Driver

### Absolute maximum ratings

Symbol	1	Parameter	Max ratings	Unit
$V_{ m DD}$	Supply Voltage		5.5	V
$V_{\mathrm{INi}}$	Input signal voltage i=L, H		5.5	·
$I_{VDDmax}$	Maximum Supply current —	$V_{INi} = 0V$ , $i = L \& H$	0.35	
		$V_{DD}=5V$ , $V_{INH}=/V_{INL}$ ; $F_{out}=45$ kHz	2	Α
$f_{max}$	Maximum Switching Frequence	cy	45	kHz

#### **Driver Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{ m DD}$	Operating Supply Voltage		4.5	5	5.5	V
V <sub>INi(max)</sub>	Maximum Input Voltage		-0.5	5	5.5	
V <sub>INi (th+)</sub>	Positive Going Threshold Voltage	i = L. H		3.2		V
$V_{INi(th-)}$	Negative Going Threshold Voltage	1 - L, n		1		
R <sub>INi</sub>	Input Resistance *			1		kΩ
$T_{d(on)}$	Turn On delay time	Driver + IGBT		1100°		
$D_{T}$	Built in dead time			600		ns
$T_{d(off)}$	Turn Off delay time	Driver + IGBT		750		
PWD	Pulse Width Distortion				300	
PDD	Propagation Delay Difference between any two driver	T <sub>d(on)</sub> - T <sub>d(off)</sub>	-350		350	ns
$V_{ISOL}$	Primary to Secondary Isolation		2500		·	$V_{RMS}$

<sup>\*</sup> Low impedance guarantees good noise immunity.

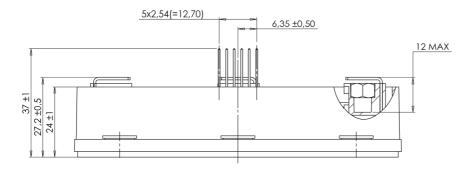
<sup>•</sup> Including built in dead time.

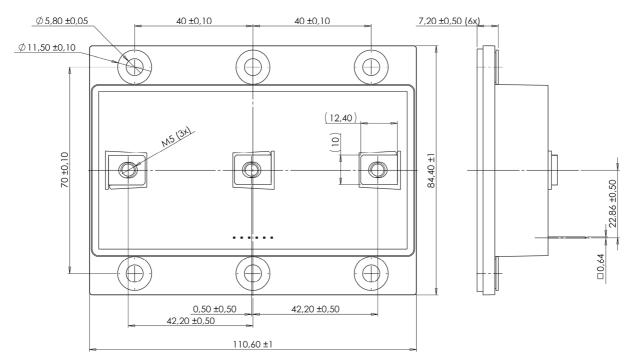


### 3. Package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V		
$T_{\mathrm{J}}$	Operating junction temperature range			-40		150			
T <sub>OP</sub>	Operating Ambient Temperature			-40		85	°C		
$T_{STG}$	Storage Temperature Range			-40		100			
$T_{\rm C}$	Operating Case Temperature			-40		100			
Torque	Mounting forgue	To heatsink	M5	2		4.7	N.m		
Torque		M5	2		4	11.111			
Wt	Package Weight				550		g		

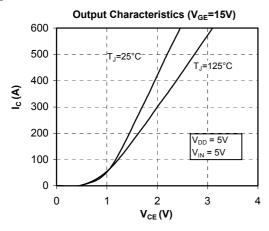
### 4. LP8 Package outline (dimensions in mm)

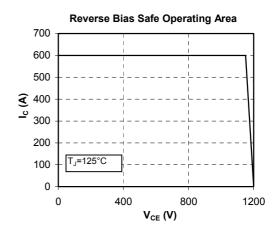


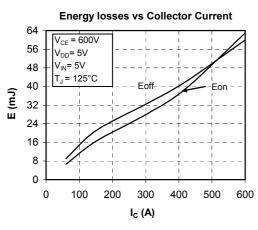


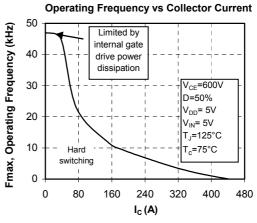


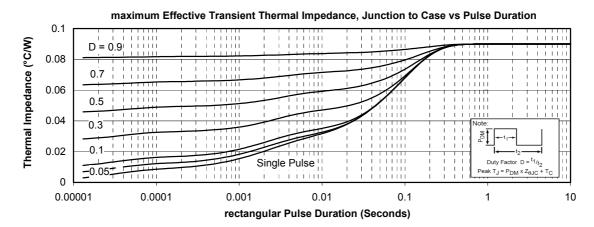
### **Typical IGBT Performance Curve**





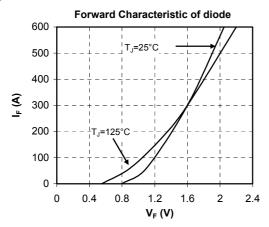


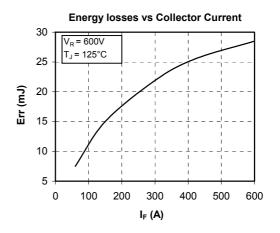


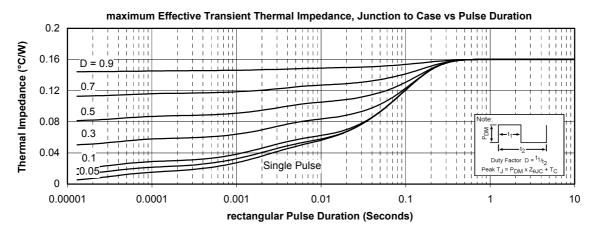




### **Typical diode Performance Curve**









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